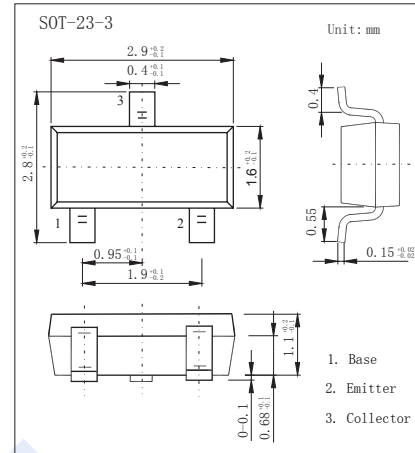


## PNP Transistors

### 2SA1621

#### ■ Features

- Collector Current Capability  $I_c = -800\text{mA}$
- Collector Emitter Voltage  $V_{CE0} = -30\text{V}$
- Complementary to 2SC4210



#### ■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

Parameter	Symbol	Rating	Unit
Collector - Base Voltage	$V_{CB0}$	-35	V
Collector - Emitter Voltage	$V_{CE0}$	-30	
Emitter - Base Voltage	$V_{EB0}$	-5	
Collector Current - Continuous	$I_c$	-800	mA
Base Current	$I_B$	-160	
Collector Power Dissipation	$P_c$	200	mW
Junction Temperature	$T_J$	150	$^\circ\text{C}$
Storage Temperature range	$T_{stg}$	-55 to 150	

#### ■ Electrical Characteristics $T_a = 25^\circ\text{C}$

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector- base breakdown voltage	$V_{CB0}$	$I_c = -100\ \mu\text{A}, I_E = 0$	-35			V
Collector- emitter breakdown voltage	$V_{CE0}$	$I_c = -10\ \text{mA}, I_B = 0$	-30			
Emitter - base breakdown voltage	$V_{EB0}$	$I_E = -100\ \mu\text{A}, I_c = 0$	-5			
Collector-base cut-off current	$I_{CB0}$	$V_{CB} = -35\ \text{V}, I_E = 0$			-0.1	$\mu\text{A}$
Emitter cut-off current	$I_{EB0}$	$V_{EB} = -5\ \text{V}, I_c = 0$			-0.1	
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_c = -500\ \text{mA}, I_B = -20\ \text{mA}$			-0.7	V
Base - emitter saturation voltage	$V_{BE(sat)}$	$I_c = -500\ \text{mA}, I_B = -20\ \text{mA}$			-1.2	
Base - emitter voltage	$V_{BE}$	$V_{CE} = -1\ \text{V}, I_c = -10\ \text{mA}$	-0.5		-0.8	
DC current gain	$h_{FE}$	$V_{CE} = -1\ \text{V}, I_c = -100\ \text{mA}$	100		320	
		$V_{CE} = -1\ \text{V}, I_c = -700\ \text{mA}$	35			
Collector output capacitance	$C_{ob}$	$V_{CB} = -10\ \text{V}, I_E = 0, f = 1\ \text{MHz}$		19		pF
Transition frequency	$f_T$	$V_{CE} = -5\ \text{V}, I_c = -10\ \text{mA}$		120		MHz

#### ■ Classification of $h_{FE}(1)$

Type	2SA1621-O	2SA1621-Y
Range	100-200	160-320
Marking	7O	7Y

### PNP Transistors

### 2SA1621

■ Typical Characteristics

